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Kind regards,

Team Nexperia



Medium power Schottky barrier single diode

Rev. 03 — 17 October 2008

Product data sheet

1. Product profile

1.1 General description

Planar medium power Schottky barrier single diode with an integrated guard ring for stress protection, encapsulated in a SOD323 (SC-76) very small Surface-Mounted Device SMD plastic package.

1.2 Features

- Ultra high-speed switching
- Very low forward voltage
- Guard-ring protected
- Very small SMD plastic package

1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{R}	reverse voltage		-	-	20	V
I _F	forward current		-	-	1	Α
V _F	forward voltage	I _F = 1 A	[1] _	480	550	mV

[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



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2. Pinning information

Table 2. Pinning

Description	Simplified outline	Graphic symbol
cathode	[1]	
anode	1 2	1 - 2
		sym001
	Description cathode	Description Simplified outline cathode

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package	ackage						
	Name	Description	Version					
BAT760	SC-76	plastic surface-mounted package; 2 leads	SOD323					

4. Marking

Table 4. Marking codes

Type number	Marking code
BAT760	A4

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	reverse voltage		-	20	V
I _F	forward current		-	1	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8.3 ms; half-sine wave; JEDEC method	-	5	Α
Tj	junction temperature		-	125	°C
T_{amb}	ambient temperature		-65	+125	°C
T _{stg}	storage temperature		-65	+150	°C

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
			[1]	-	220	K/W
			[2]	-	180	K/W

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for cathode $10 \times 10 \text{ mm}^2$.

7. Characteristics

Table 7. Characteristics

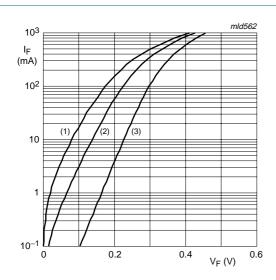
T_{amb} = 25 °C unless otherwise specified.

		•				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
		I _F = 10 mA	-	240	270	mV
		$I_F = 100 \text{ mA}$	-	300	350	mV
		I _F = 1 A	-	480	550	mV
I _R reverse current			<u>[1]</u>			
		$V_R = 5 V$	-	5	10	μΑ
		$V_R = 8 V$	-	7	20	μΑ
		V _R = 15 V	-	10	50	μΑ
C_d	diode capacitance	$V_R = 5 V$; $f = 1 MHz$	-	19	25	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

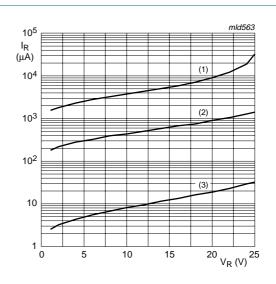
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode $40 \times 40 \text{ mm}^2$.

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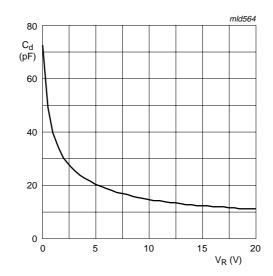
- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

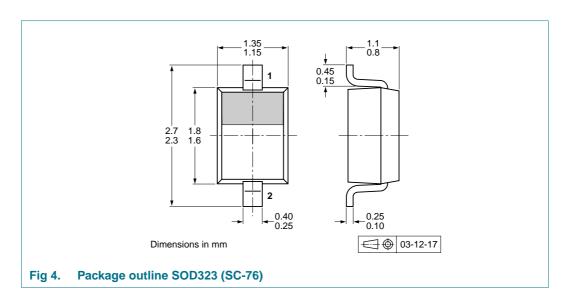


f = 1 MHz; T_{amb} = 25 °C

Fig 3. Diode capacitance as a function of reverse voltage; typical values

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8. Package outline



9. Packing information

Table 8. Packing methods

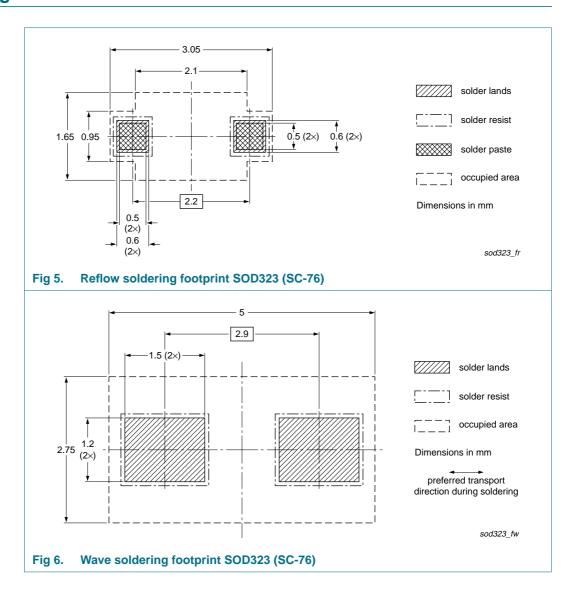
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BAT760	SOD323	4 mm pitch, 8 mm tape and reel	-115	-135

^[1] For further information and the availability of packing methods, see Section 13.

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10. Soldering



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11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BAT760_3	20081017	Product data sheet	-	BAT760_2			
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 						
 Legal texts have been adapted to the new company name where appropriate. Table 1 "Quick reference data": added 							
							 Figure 4: superseded by minimized package outline drawing
	 Section 9 "Pack 	ing information": added					
	Section 10 "Solo	dering": added					
	Section 12 "Leg	al information": updated					
BAT760_2	20040126	Product specification	-	BAT760_1			
BAT760_1	20010312	Product specification	-	-			

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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